MJB41C, NJVMJB41CT4G (NPN), MJB42C, NJVMJB42CT4G (PNP)

Complementary Silicon Plastic Power Transistors

D²PAK for Surface Mount

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Electrically the Same as TIP41 and T1P42 Series
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	100	Vdc
Collector-Base Voltage	V _{CB}	100	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current – Continuous – Peak	Ic	6.0 10	Adc
Base Current	Ι _Β	2.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	65 0.52	W W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016	W W/°C
Unclamped Inductive Load Energy (Note 1)	E	62.5	mJ
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.92	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	50	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from Case for 10 Seconds	TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. I_C = 2.5 A, L = 20 mH, P.R.F. = 10 Hz, V_{CC} = 10 V, R_{BE} = 100 Ω
- When surface mounted to an FR-4 board using the minimum recommended pad size.



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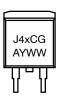
http://onsemi.com

COMPLEMENTARY SILICON POWER TRANSISTORS 6 AMPERES, 100 VOLTS, 65 WATTS

MARKING DIAGRAM



D²PAK CASE 418B STYLE 1



J4xC = Specific Device Code

x = 1 or 2

= Assembly Location

= Year

WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MJB41CG	D ² PAK (Pb-Free)	50 Units / Rail
MJB41CT4G	D ² PAK (Pb-Free)	800 / Tape & Reel
NJVMJB41CT4G	D ² PAK (Pb-Free)	800 / Tape & Reel
MJB42CG	D ² PAK (Pb-Free)	50 Units / Rail
MJB42CT4G	D ² PAK (Pb-Free)	800 / Tape & Reel
NJVMJB42CT4G	D ² PAK (Pb-Free)	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

V _{CEO(sus)} I _{CEO}	100	- 0.7	Vdc
I _{CEO}	100	- 0.7	Vdc
+ .	-	0.7	
I _{CES}		0.7	mAdc
	_	100	μAdc
I _{EBO}	_	50	μAdc
h _{FE}	30 15	- 75	-
V _{CE(sat)}	-	1.5	Vdc
V _{BE(on)}	-	2.0	Vdc
•			
f _T	3.0	_	MHz
hea	20		
	V _{CE(sat)}	15 V _{CE(sat)} - V _{BE(on)} -	15 75 V _{CE(sat)} - 1.5 V _{BE(on)} - 2.0 f _T 3.0 -

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

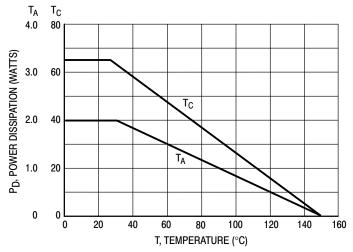
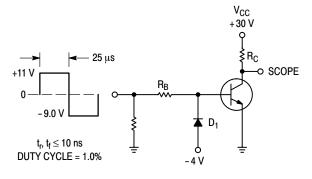


Figure 1. Power Derating



 $\ensuremath{\mathsf{R}}_B$ and $\ensuremath{\mathsf{R}}_C$ varied to obtain desired current levels

D $_1$ MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE IB $\approx 100~\text{mA}$ MSD6100 USED BELOW IB $\approx 100~\text{mA}$

Figure 2. Switching Time Test Circuit

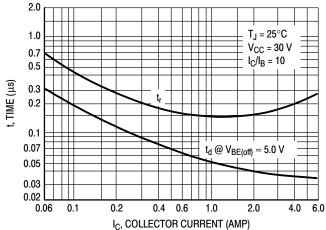


Figure 3. Turn-On Time

MJB41C, NJVMJB41CT4G (NPN), MJB42C, NJVMJB42CT4G (PNP)

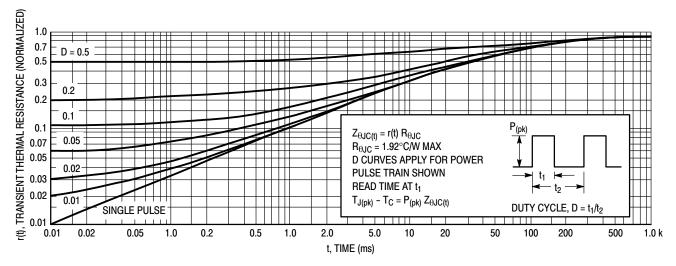


Figure 4. Thermal Response

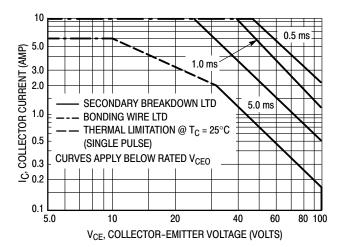


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ} C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ} C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

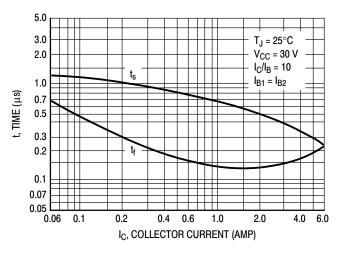


Figure 6. Turn-Off Time

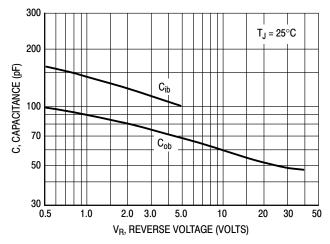


Figure 7. Capacitance

MJB41C, NJVMJB41CT4G (NPN), MJB42C, NJVMJB42CT4G (PNP)

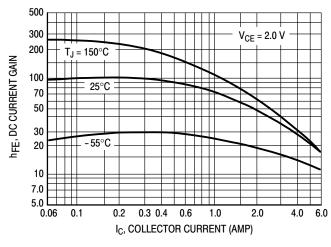


Figure 8. DC Current Gain

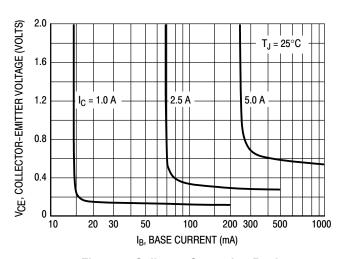


Figure 9. Collector Saturation Region

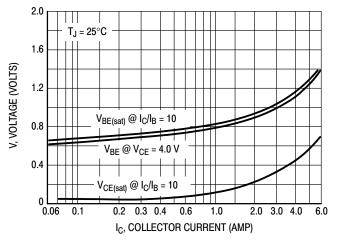


Figure 10. "On" Voltages

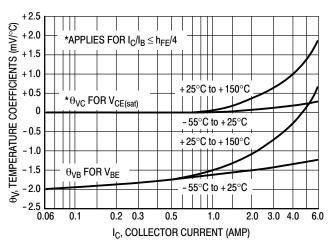


Figure 11. Temperature Coefficients

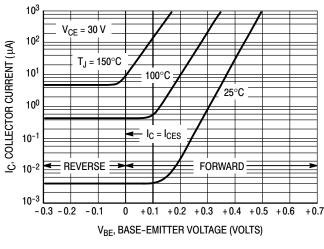


Figure 12. Collector Cut-Off Region

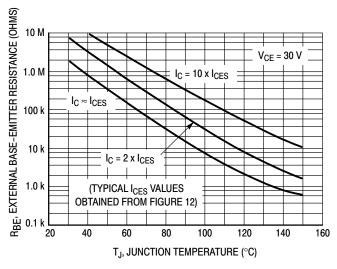


Figure 13. Effects of Base-Emitter Resistance

MECHANICAL CASE OUTLINE

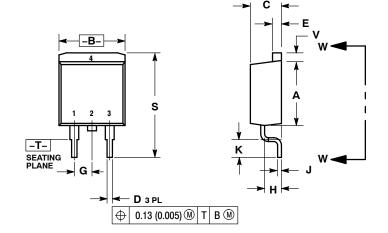




D²PAK 3 CASE 418B-04 **ISSUE L**

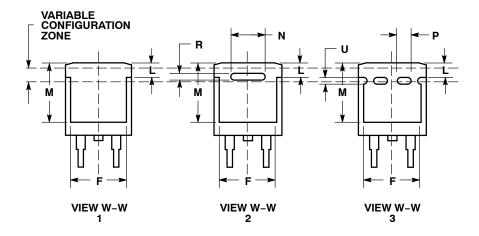
DATE 17 FEB 2015

SCALE 1:1



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INC	HES	MILLIM	IETERS
ым	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
Н	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
Р	0.079 REF		2.00 REF	
R	0.039	REF	0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6: PIN 1. NO CONNECT 2. CATHODE 3. ANODE 4. CATHODE

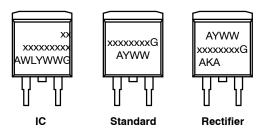
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GENERIC MARKING DIAGRAM*



xx = Specific Device Code A = Assembly Location

 WL
 = Wafer Lot

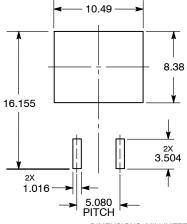
 Y
 = Year

 WW
 = Work Week

 G
 = Pb-Free Package

 AKA
 = Polarity Indicator

SOLDERING FOOTPRINT*



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